

Product data sheet

1. **Product profile**

1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT78 (TO-220AB) plastic package.

1.2 Features and benefits

Low thermal resistance

Fast switching

1.3 Applications

- Electronic lighting ballasts
- Inverters

- DC-to-DC converters
- Motor control systems

1.4 Quick reference data

- V_{CESM} ≤ 700 V
- Arr P_{tot} \leq 80 W

- $I_C \le 4 A$
- h_{FEsat} = 12.5 (typ)

Pinning information

Table 1. **Pinning**

Pin	Description	Simplified outline	Symbol
1	base		
2	collector	mb	2
3	emitter	705	1—
mb	mounting base; connected to collector	1 2 3	3 sym056
		SOT78 (TO-220AB)	



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3. Ordering information

Table 2. Ordering information

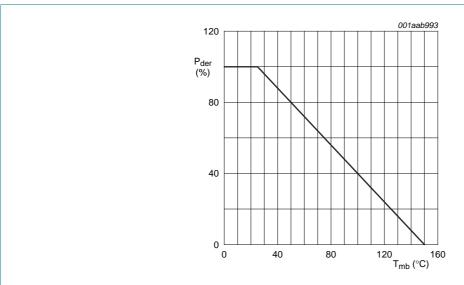
Type number	Package	Package						
	Name	Description	Version					
BUJ103A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-leads	SOT78					

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	peak collector-emitter voltage	$V_{BE} = 0 V$	-	700	V
V_{CBO}	collector-base voltage	open emitter	-	700	V
V_{CEO}	collector-emitter voltage	open base	-	400	V
I _C	collector current (DC)		-	4	Α
I _{CM}	peak collector current		-	8	Α
I _B	base current (DC)		-	2	Α
I_{BM}	peak base current		-	4	Α
P _{tot}	total power dissipation	$T_{mb} \le 25$ °C; see Figure 1	-	80	W
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C



$$P_{der}(\%) = \frac{P_{tot}}{P_{tot(25 °C)}} \times 100\%$$

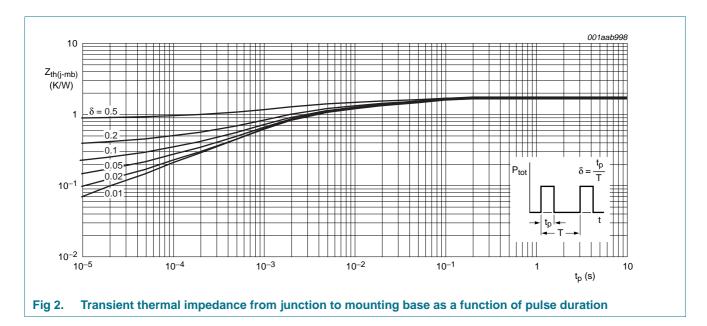
Fig 1. Normalized total power dissipation as a function of mounting base temperature

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5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 2	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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6. Characteristics

Table 5. Characteristics

 T_{mb} = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{CES}	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = V _{CESMmax}	[1] -	-	1	mΑ
	current	$V_{BE} = 0 \text{ V}; V_{CE} = V_{CESMmax}; T_j = 125 ^{\circ}\text{C}$	<u>[1]</u> -	-	2	mΑ
I _{CBO}	collector-base cut-off current	V _{BE} = 0 V; V _{CE} = V _{CESMmax}	<u>[1]</u> -	-	1	mΑ
I _{CEO}	collector-emitter cut-off current	$V_{CEO} = V_{CEOMmax} = 400 \text{ V}$	[1] -	-	0.1	mA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V; } I_{C} = 0 \text{ A}$	-	-	0.1	mΑ
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}$; $I_C = 10 \text{ mA}$; $L = 25 \text{ mH}$; see Figure 3 and 4	400	-	-	V
V _{CEsat}	collector-emitter saturation voltage	$I_C = 3.0 \text{ A}$; $I_B = 0.6 \text{ A}$; see <u>Figure 10</u>	-	0.25	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 3.0 \text{ A}$; $I_B = 0.6 \text{ A}$; see <u>Figure 11</u>	-	0.97	1.5	V
h _{FE} DC current gain	DC current gain	I _C = 1 mA; V _{CE} = 5 V; see <u>Figure 9</u>	10	17	32	
		$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}$	13	22	32	
h _{FEsat}	DC saturation current gain	I _C = 2.0 A; V _{CE} = 5 V	11	16	22	
		$I_C = 3.0 \text{ A}; V_{CE} = 5 \text{ V}$	-	12.5	-	
Dynamic o	characteristics					
Switching t	imes (resistive load); see Figure	<u>5</u> and <u>6</u>				
t _{on}	turn-on time	$I_{Con} = 2.5 \text{ A}; I_{Bon} = -I_{Boff} = 0.5 \text{ A};$	-	0.52	0.6	μS
t _{stg}	storage time	$R_L = 75 \Omega$	-	2.7	3.3	μS
t _f	fall time		-	0.3	0.35	μS
Switching t	imes (inductive load); see Figure	<u>7</u> and <u>8</u>				
t _{stg}	storage time	$I_{Con} = 2 \text{ A}$; $I_{Bon} = 0.4 \text{ A}$; $L_{B} = 1 \mu\text{H}$;	-	1.2	1.4	μS
t _f	fall time	$V_{BB} = -5 \text{ V}$	-	30	60	ns
Switching t	imes (inductive load); see Figure	<u>7</u> and <u>8</u>				
t _{stg}	storage time	$I_{Con} = 2 \text{ A}$; $I_{Bon} = 0.4 \text{ A}$; $L_{B} = 1 \mu\text{H}$;	-	-	1.8	μS
t _f	fall time	$V_{BB} = -5 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	-	120	ns

^[1] Measured with half sine-wave voltage (curve tracer).

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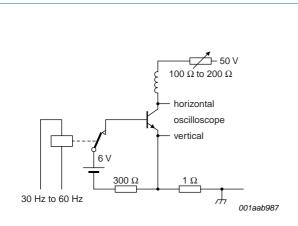


Fig 3. Test circuit for collector-emitter sustaining voltage

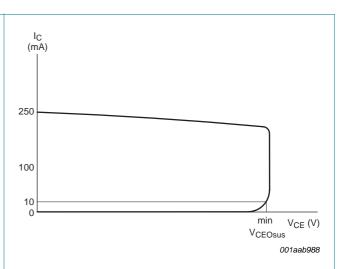
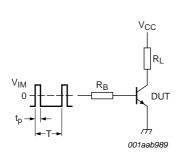


Fig 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



 V_{IM} = -6 V to +8 V; V_{CC} = 250 V; t_p = 20 $\mu s;$ δ = t_p/T = 0.01.

 R_{B} and R_{L} calculated from I_{Con} and I_{Bon} requirements.

Fig 5. Test circuit for resistive load switching

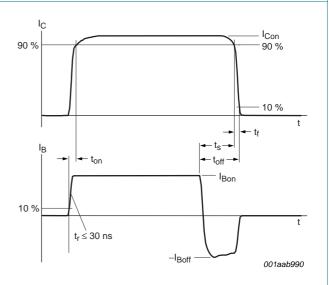
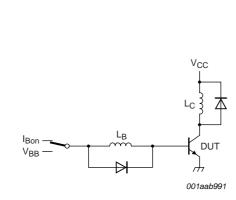


Fig 6. Switching times waveforms for resistive load

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 V_{CC} = 300 V; V_{BB} = -5 V; L_{C} = 200 $\mu H;$ L_{B} = 1 $\mu H.$

Fig 7. Test circuit for inductive load switching

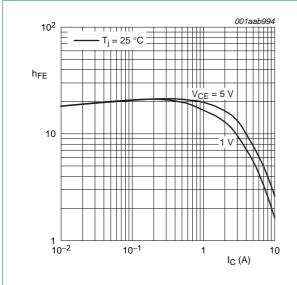


Fig 9. DC current gain as a function of collector current; typical values

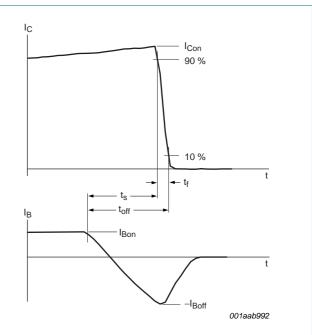
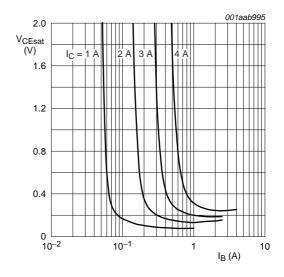


Fig 8. Switching times waveforms for inductive load



 $T_i = 25 \, ^{\circ}C$.

Fig 10. Collector-emitter saturation voltage as a function of base current; typical values

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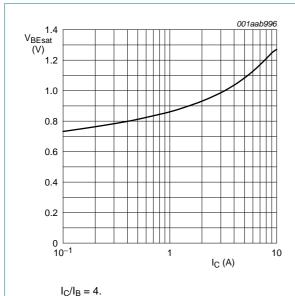
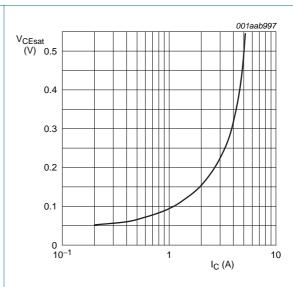
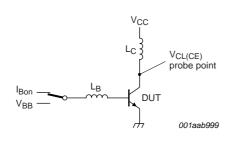


Fig 11. Base-emitter saturation voltage as a function of collector current; typical values



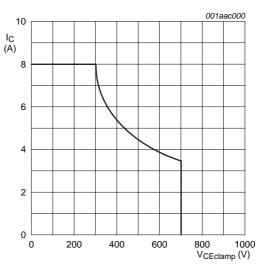
 $I_{C}/I_{B} = 4$.

Fig 12. Collector-emitter saturation voltage as a function of collector current; typical values



 $V_{CEclamp} \leq$ 1000 V; V_{CC} = 150 V; V_{BB} = -5 V; L_B = 1 μH ; L_C = 200 μH .

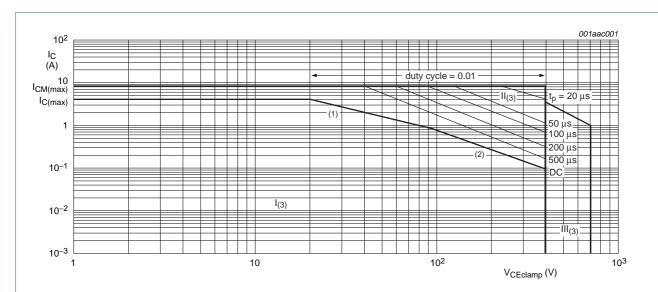
Fig 13. Test circuit for reverse bias safe operating area



 $T_j \leq T_{j(max)}$.

Fig 14. Reverse bias safe operating area

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 T_{mb} \leq 25 °C; Mounted with heatsink compound and 30 \pm 5 Newton force on the center of the envelope.

- (1) Ptot maximum and Ptot peak maximum lines.
- (2) Second breakdown limits.
- (3) I = Region of permissible DC operation.
 - II = Extension for repetitive pulse operation.
 - III = Extension during turn-on in single transistor converters provided that $R_{BE} \le 100~\Omega$ and $t_p \le 0.6~\mu s$.

Fig 15. Forward bias safe operating area

7. Package information

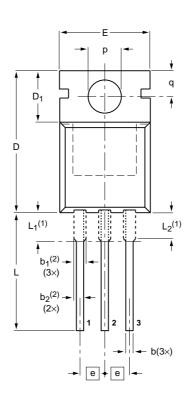
Epoxy meets requirements of UL94 V-0 at ½ inch.

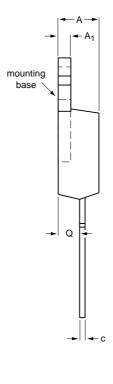
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Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**





0 5 10 mm scale

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ (2)	b ₂ (2)	C	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	ø
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
 Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig 16. Package outline SOT78 (TO-220AB)

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9. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ103A v.4	20111108	Product data sheet	-	BUJ103A v.3
Modifications:	guidelines	of this data sheet has been of NXP Semiconductors. have been adapted to the r		·
BUJ103A v.3	20050303	Product data sheet	-	BUJ103A HG v.2
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BUJ103A_HG v.2	19980918	Product data sheet	-	BUJ103A v.1

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10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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